29th RD50 Workshop (CERN)

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New results of measurements with irradiated CMOS detectors in Ljubljana

Monday 21 November 2016 10:15 (20 minutes)

New results of E-TCT and Sr90 measurements with CMOS detectors produced on substrates with different resistivities will be presented. With Edge-TCT method the thickness of depleted layer can be estimated and its dependence on irradiation flunece was studied. Collected charge deposited by MIPs from Sr90 source in passive CMOS detectors was measured with external amplifier. The dependence of collected charge on fluence will be presented and compared to E-TCT measurements.

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